

NTSX2102

Dual supply translating transceiver; open-drain; auto direction sensing

Rev. 2.1 — 12 November 2021

Product data sheet

1 General description

The NTSX2102 is a 2-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation. It features two 2-bit input-output ports (An and Bn), one output enable input (OE) and two supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both supplies can be supplied at any voltage between 1.65 V and 5.5 V. This flexibility makes the device suitable for translating between any of the voltage nodes (1.8 V, 2.5 V, 3.3 V, and 5.0 V). Pins An and OE are referenced to $V_{CC(A)}$ and pins Bn are referenced to $V_{CC(B)}$. A LOW level at pin OE causes the outputs to assume a high-impedance OFF-state. This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2 Features and benefits

- Wide supply voltage range:
 - $V_{CC(A)}$: 1.65 V to 5.5 V and $V_{CC(B)}$: 1.65 V to 5.5 V
- Maximum data rates:
 - 50 Mbit/s
- I_{OFF} circuitry provides partial power-down mode operation
- Inputs accept voltages up to 5.5 V
- ESD protection:
 - HBM JS-001 Class 2 exceeds 2000 V
 - CDM JESD22-C101E exceeds 2000 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$

3 Applications

- I²C/SMBus
- UART
- GPIO



4 Ordering information

Table 1. Ordering information

Type number	Topside marking	Package		
		Name	Description	Version
NTSX2102GU8	sX	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.4 × 1.2 × 0.5 mm	SOT1309-1
NTSX2102GD	sX2	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 × 2 × 0.5 mm	SOT996-2
NTSX2102TL	tX2	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 × 2 × 0.5 mm	SOT1052-2

4.1 Ordering options

Table 2. Ordering options

Type number	Orderable part number	Package	Packing method ^[1]	Minimum order quantity	Temperature
NTSX2102GU8	NTSX2102GU8H	XQFN8	Reel 7" Q3 NDP	4000	-40 °C to +85 °C
NTSX2102GD ^[2]	NTSX2102GDH	XSON8	Reel 7" Q3 NDP	3000	-40 °C to +85 °C
NTSX2102TL	NTSX2102TLH	XSON8	Reel 7" Q3 NDP	3000	-40 °C to +85 °C

[1] Standard packing quantities and other packaging data are available at www.nxp.com/packages/.

[2] Discontinuation Notice 202111012DN - drop in replacement is NTSX0102TLH.

5 Functional diagram

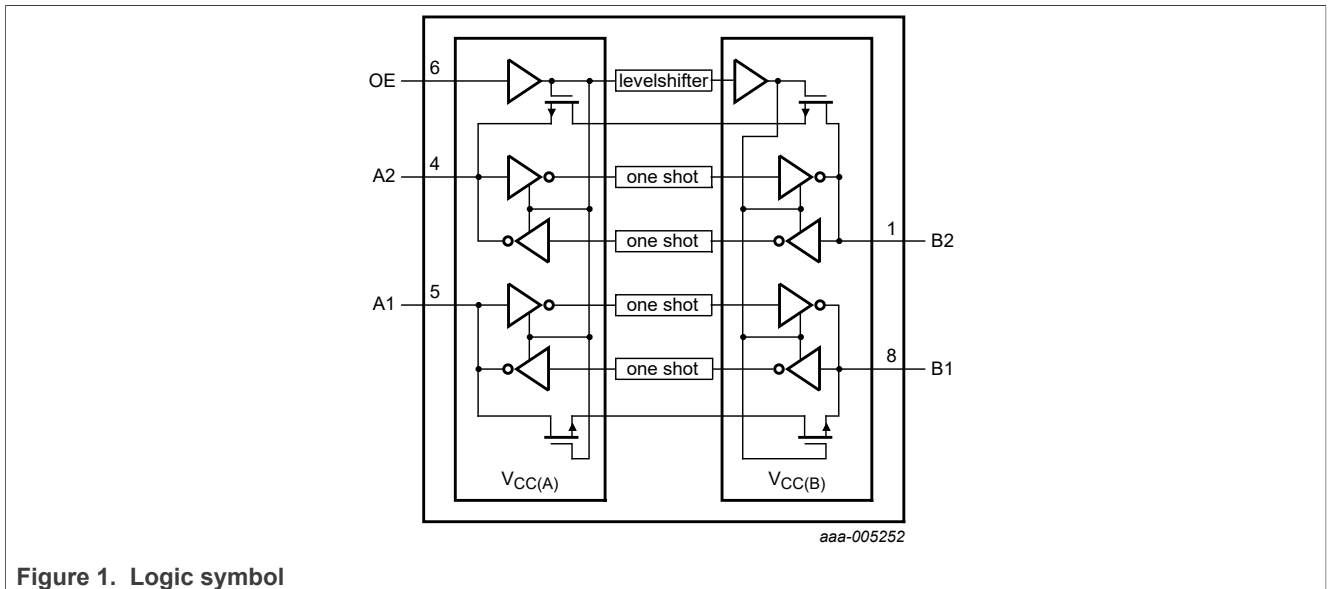
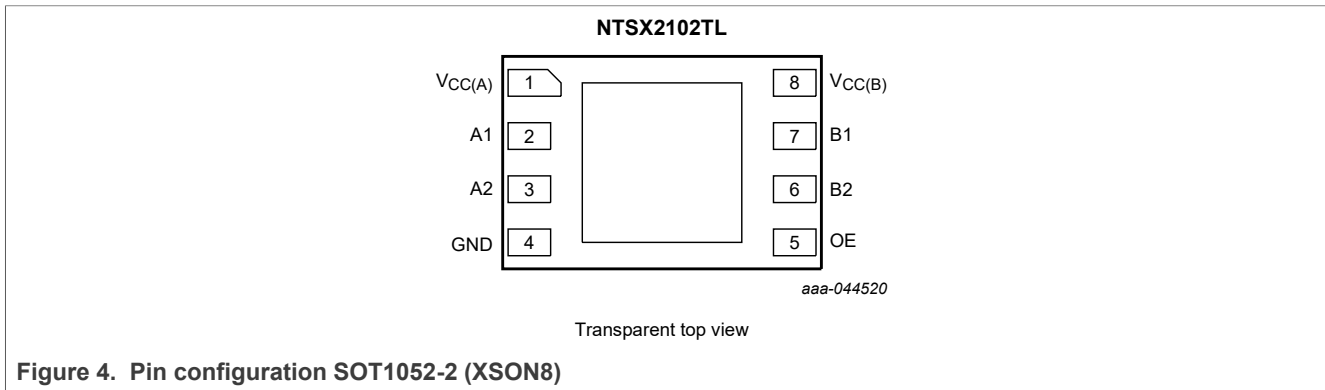
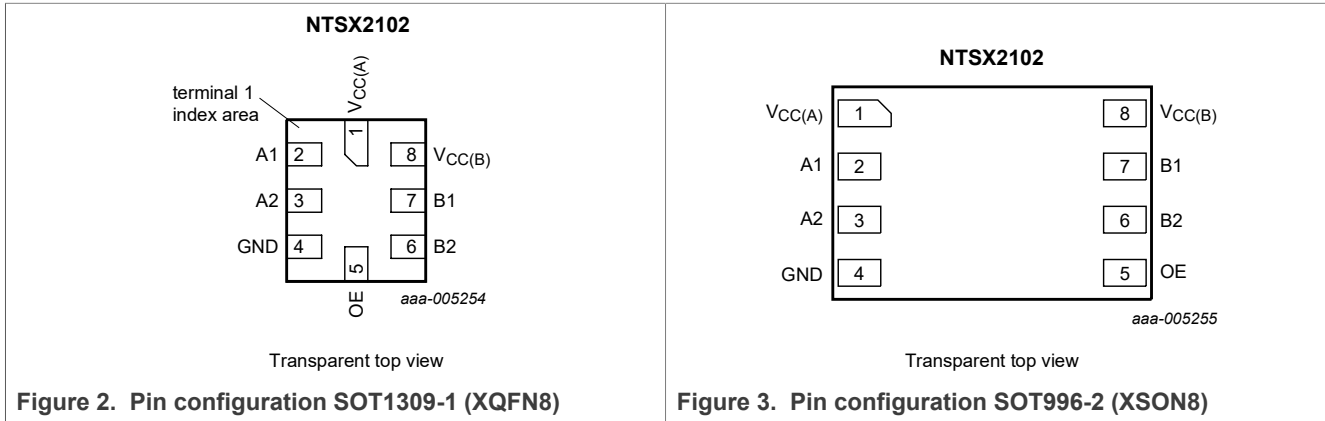


Figure 1. Logic symbol

6 Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B2, B1	6, 7	data input or output (referenced to $V_{CC(B)}$)
GND	4	ground (0 V)
$V_{CC(A)}$	1	supply voltage A
A2, A1	3, 2	data input or output (referenced to $V_{CC(A)}$)
OE	5	output enable input (active HIGH; referenced to $V_{CC(A)}$)
$V_{CC(B)}$	8	supply voltage B

7 Functional description

Table 4. Function table^[1]

Supply voltage		Input	Input/output	
V _{CC(A)}	V _{CC(B)}	OE	An	Bn
1.65 V to 5.5 V	1.65 V to 5.5 V	L	Z	Z
1.65 V to 5.5 V	1.65 V to 5.5 V	H	input or output	output or input
GND ^[2]	GND ^[2]	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] When either V_{CC(A)} or V_{CC(B)} is at GND level, the device goes into power-down mode.

8 Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		-0.5	+6.5	V
V _{CC(B)}	supply voltage B		-0.5	+6.5	V
V _I	input voltage	A port and OE input ^{[1] [2]}	-0.5	+6.5	V
		B port ^{[1] [2]}	-0.5	+6.5	V
V _O	output voltage	Active mode ^{[1] [2]}			
		A or B port	-0.5	V _{CCO} + 0.5	V
		Power-down or 3-state mode ^[1]			
	A or B port	-0.5	+6.5	V	
I _{IK}	input clamping current	V _I < 0 V	-50	—	mA
I _{OK}	output clamping current	V _O < 0 V	-50	—	mA
I _O	output current	V _O = 0 V to V _{CCO} ^[2]	—	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}	—	100	mA
I _{GND}	ground current		-100	—	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +85 °C	—	250	mW

[1] If the input and output current ratings are observed, the minimum input and minimum output voltage ratings may be exceeded.

[2] V_{CCO} is the supply voltage associated with the output.

9 Recommended operating conditions

Table 6. Recommended operating conditions^[1]

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		1.65	5.5	V
V _{CC(B)}	supply voltage B		1.65	5.5	V

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Table 6. Recommended operating conditions^[1]...continued

Symbol	Parameter	Conditions	Min	Max	Unit
T _{amb}	ambient temperature		-40	+85	°C
Δt/ΔV	input transition rise and fall rate	A, B or OE port			
		V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 1.65 V to 5.5 V	—	10	ns/V

[1] Hold the A and B sides of an unused I/O pair in the same state, both at V_{CCI} or both at GND.

10 Static characteristics

Table 7. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C _I	input capacitance	OE input; V _{CC(A)} = V _{CC(B)} = 0 V	—	2.2	—	pF
C _{I/O}	input/output capacitance	A or B port; V _{CC(A)} = 5.0 V; V _{CC(B)} = 5.0 V	—	10	—	pF

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C		Unit
			Min	Max	
V _{IH}	HIGH-level input voltage	A or B port			
		V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 1.65 V to 5.5 V ^[1]	V _{CCI} - 0.4	—	V
		OE input			
		V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 1.65 V to 5.5 V	0.65V _{CC(A)}	—	V
V _{IL}	LOW-level input voltage	A or B port			
		V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 1.65 V to 5.5 V	—	0.4	V
		OE input			
		V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 1.65 V to 5.5 V	—	0.35V _{CC(A)}	V
V _{OL}	LOW-level output voltage	A or B port; I _O = 6 mA ^[2]			
		V _I ≤ 0.15 V; V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 1.65 V to 5.5 V	—	0.4	V
I _I	input leakage current	OE input; V _I = 0 V to V _{CC(A)} ; V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 1.65 V to 5.5 V	—	±1	μA
I _{OZ}	OFF-state output current	A or B port; V _O = 0 V or V _{CCO} ; V _{CC(A)} = 0 V to 5.5 V; V _{CC(B)} = 0 V to 5.5 V ^[2]	—	±2	μA
I _{OFF}	power-off leakage current	A port; V _I or V _O = 0 V to 5.5 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0 V to 5.5 V	—	±2	μA
		B port; V _I or V _O = 0 V to 5.5 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0 V to 5.5 V	—	±2	μA

Table 8. Static characteristics...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C		Unit
			Min	Max	
I _{CC}	supply current	V _I = 0 V or V _{CCI} ; I _O = 0 A ^[1]			
		I _{CC(A)}			
		V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 1.65 V to 5.5 V; OE = LOW or HIGH	—	5	µA
		V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 0 V	—	2	µA
		V _{CC(A)} = 0 V; V _{CC(B)} = 1.65 V to 5.5 V	—	-2	µA
		I _{CC(B)}			
		V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 1.65 V to 5.5 V; OE = LOW	—	5	µA
		V _{CC(A)} = 1.65 V to 5.5 V; V _{CC(B)} = 0 V	—	-2	µA
		V _{CC(A)} = 0 V; V _{CC(B)} = 1.65 V to 5.5 V	—	2	µA

[1] V_{CCI} is the supply voltage associated with the input.
 [2] V_{CCO} is the supply voltage associated with the output.

11 Dynamic characteristics

Table 9. Typical dynamic characteristics for temperature 25 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for waveforms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions	V _{CCO} ^[1]				Unit
			1.8 V	2.5 V	3.3 V	5.0 V	
t _{TLH}	LOW to HIGH output transition time	A or B port	7	5	4	3	ns
t _{THL}	HIGH to LOW output transition time	A or B port	4	6	8	11	ns
C _{PD}	power dissipation capacitance	OE = V _{CC(A)} ; V _{CC(A)} = V _{CC(B)} ; ^[3] f _i = 400 kHz; V _I = V _{CCI} ^[2]	—	—	—	13.5	pF

[1] V_{CCO} is the supply voltage associated with the output.
 [2] V_{CCI} is the supply voltage associated with the input.
 [3] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

Dual supply translating transceiver; open-drain; auto direction sensing

Table 10. Dynamic characteristics for temperature range -40 °C to +85 °C^[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions	V _{CC(B)}								Unit
			1.8 V ± 0.15 V		2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Typ	Max	Typ	Max	Typ	Max	Typ	Max	
V_{CC(A)} = 1.8 V ± 0.15 V											
t _{PHL}	HIGH to LOW propagation delay	A to B	3	7	3	6	3	5	5	7	ns
t _{PLH}	LOW to HIGH propagation delay	A to B	5	12	5	8	4	8	4	7	ns
t _{PHL}	HIGH to LOW propagation delay	B to A	3	7	3	6	3	5	5	7	ns
t _{PLH}	LOW to HIGH propagation delay	B to A	5	12	1	3	1	2	1	2	ns
t _{PZL}	OFF-state to LOW propagation delay	OE to A	9	16	9	18	10	14	10	15	ns
		OE to B	9	16	6	12	6	12	6	14	ns
t _{PLZ}	LOW to OFF-state propagation delay	OE to A	100	120	100	120	100	120	100	120	ns
		OE to B	100	120	100	120	100	120	100	120	ns
t _{sk(o)}	output skew time	between channels ^[2]	—	1	—	1	—	1	—	1	ns
f _{data}	data rate		—	18	—	18	—	18	—	18	Mbit/s
V_{CC(A)} = 2.5 V ± 0.2 V											
t _{PHL}	HIGH to LOW propagation delay	A to B	3	6	2	5	2	5	2	5	ns
t _{PLH}	LOW to HIGH propagation delay	A to B	1	3	2	4	2.5	7	2.5	5	ns
t _{PHL}	HIGH to LOW propagation delay	B to A	3	6	2	5	2	5	2	5	ns
t _{PLH}	LOW to HIGH propagation delay	B to A	5	8	2	4	1.5	3	1	3	ns
t _{PZL}	OFF-state to LOW propagation delay	OE to A	6	12	5	10	8	10	5	8	ns
		OE to B	9	18	5	10	4.5	9	4	8	ns
t _{PLZ}	LOW to OFF-state propagation delay	OE to A	100	120	100	120	100	120	100	120	ns
		OE to B	100	120	100	120	100	120	100	120	ns
t _{sk(o)}	output skew time	between channels ^[2]	—	1	—	1	—	1	—	1	ns
f _{data}	data rate		—	18	—	32	—	32	—	32	Mbit/s
V_{CC(A)} = 3.3 V ± 0.3 V											
t _{PHL}	HIGH to LOW propagation delay	A to B	3	5	2	5	2	4	2	4	ns
t _{PLH}	LOW to HIGH propagation delay	A to B	1	2	1.5	3	1.5	3	2	4	ns

Dual supply translating transceiver; open-drain; auto direction sensing

Table 10. Dynamic characteristics for temperature range -40 °C to +85 °C^[1]...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions	V _{CC(B)}								Unit
			1.8 V ± 0.15 V		2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Typ	Max	Typ	Max	Typ	Max	Typ	Max	
t _{PHL}	HIGH to LOW propagation delay	B to A	3	5	2	5	2	4	2	4	ns
t _{PLH}	LOW to HIGH propagation delay	B to A	4	8	2.5	7	1.5	3	1	3	ns
t _{PZL}	OFF-state to LOW propagation delay	OE to A	6	12	4.5	9	6	9	4	7	ns
		OE to B	10	14	5	10	6	9	4	8	ns
t _{PLZ}	LOW to OFF-state propagation delay	OE to A	100	120	100	120	100	120	100	120	ns
		OE to B	100	120	100	120	100	120	100	120	ns
t _{sk(o)}	output skew time	between channels ^[2]	—	1	—	1	—	1	—	1	ns
f _{data}	data rate		—	18	—	32	—	40	—	40	Mbit/s
V_{CC(A)} = 5.0 V ± 0.5 V											
t _{PHL}	HIGH to LOW propagation delay	A to B	5	7	2	5	2	4	2	4	ns
t _{PLH}	LOW to HIGH propagation delay	A to B	1	2	1	3	1	3	1	3	ns
t _{PHL}	HIGH to LOW propagation delay	B to A	5	7	2	5	2	4	2	4	ns
t _{PLH}	LOW to HIGH propagation delay	B to A	4	7	2.5	5	2	4	1	3	ns
t _{PZL}	OFF-state to LOW propagation delay	OE to A	6	14	4	8	4	8	3	5	ns
		OE to B	10	15	5	8	4	7	4	5	ns
t _{PLZ}	LOW to OFF-state propagation delay	OE to A	100	120	100	120	100	120	100	120	ns
		OE to B	100	120	100	120	100	120	100	120	ns
t _{sk(o)}	output skew time	between channels ^[2]	—	1	—	1	—	1	—	1	ns
f _{data}	data rate		—	18	—	32	—	40	—	52	Mbit/s

[1] All typical values are measured at nominal V_{CC} and T_{amb} = 25 °C.

[2] Skew between any two outputs of the same package switching in the same direction.

12 Waveforms

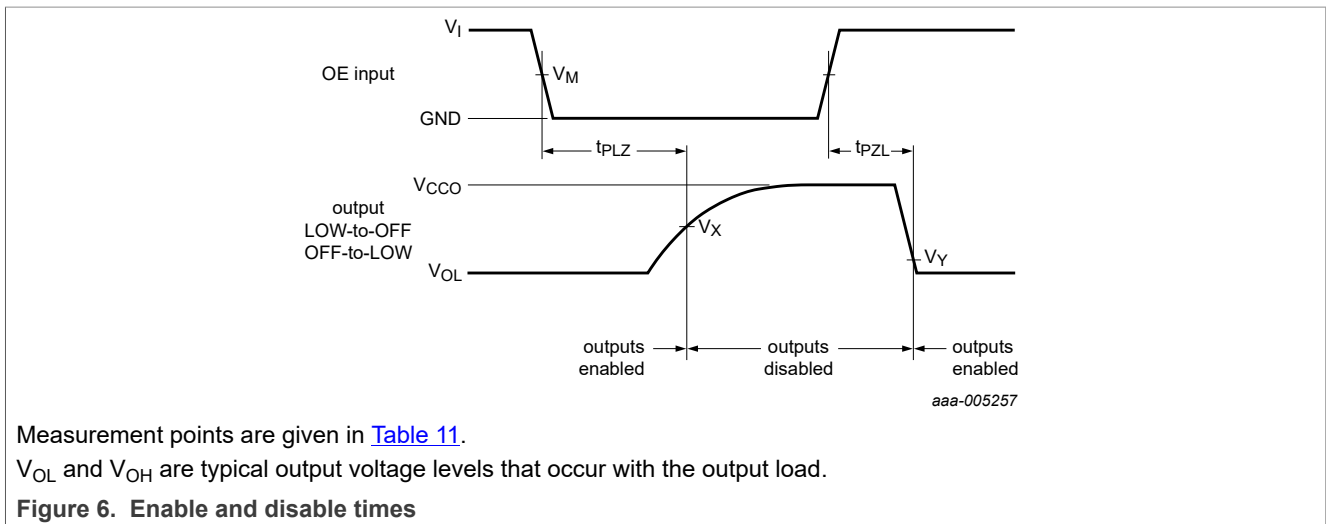
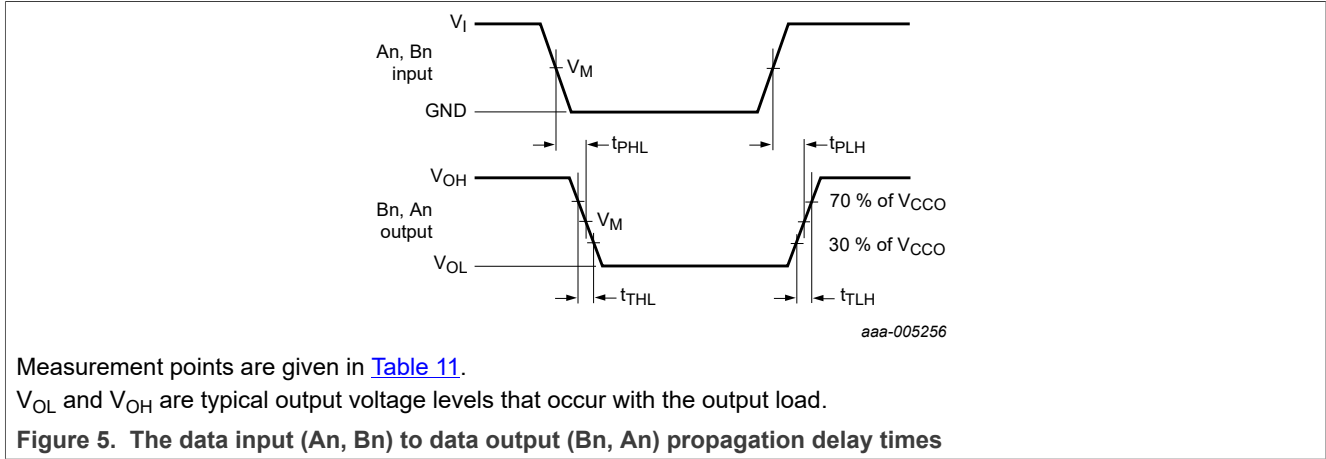


Table 11. Measurement points^{[1][2]}

Supply voltage	Input	Output		
V_{CCO}	V_M	V_M	V_X	V_Y
1.65 V to 5.5 V	$0.5V_{CCI}$	$0.5V_{CCO}$	$0.5V_{CCO}$	$0.1V_{CCO}$

[1] V_{CCI} is the supply voltage associated with the input.
 [2] V_{CCO} is the supply voltage associated with the output.

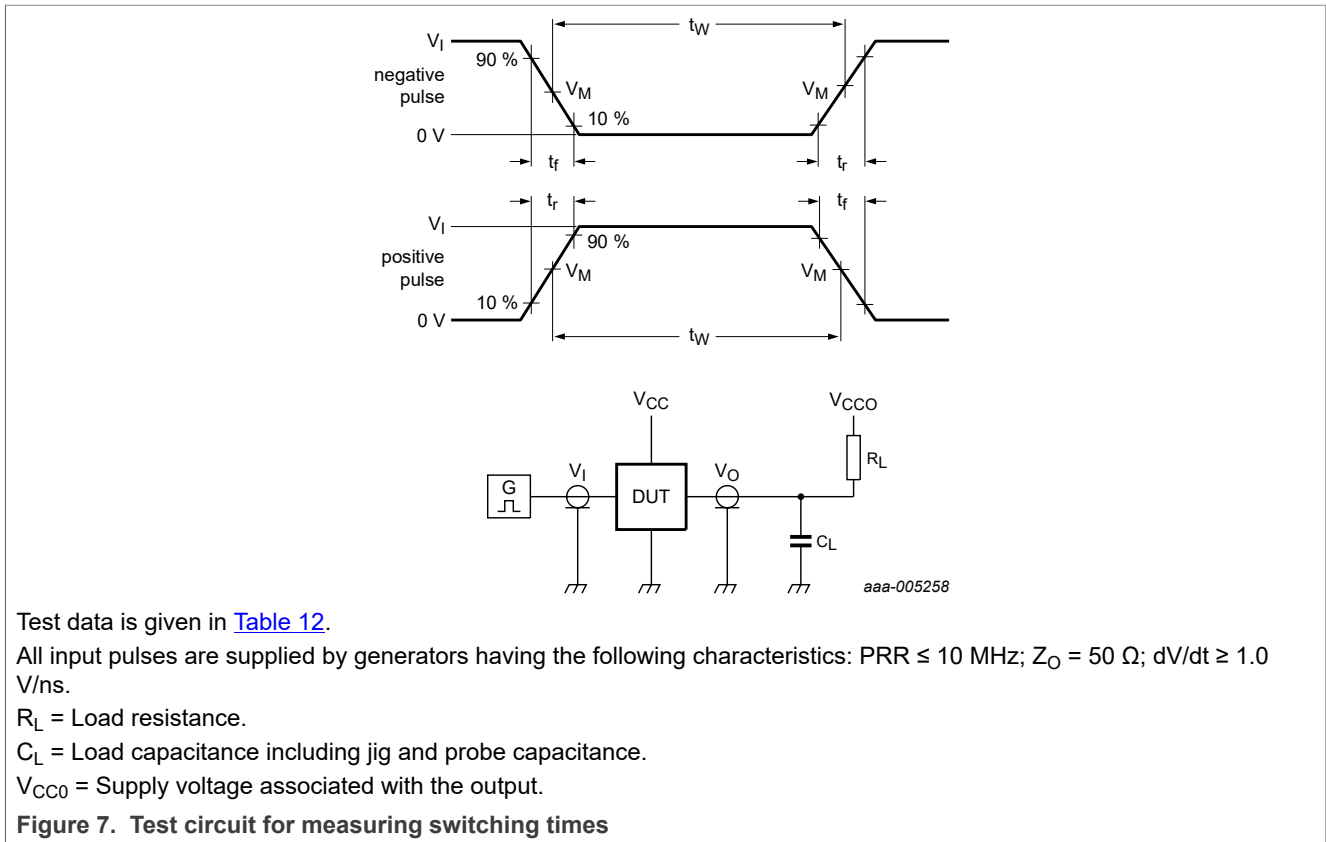


Table 12. Test data

Supply voltage		Input		Load	
V _{CC(A)}	V _{CC(B)}	V _I ^[1]	t _r /t _f	C _L	R _L
1.65 V to 1.95 V	1.65 V to 1.95 V	V _{CCi}	≤ 2.0 ns	50 pF	2.2 kΩ
2.3 V to 2.7 V	2.3 V to 2.7 V	V _{CCi}	≤ 2.0 ns	50 pF	2.2 kΩ
3.0 V to 3.6 V	3.0 V to 3.6 V	V _{CCi}	≤ 2.5 ns	50 pF	2.2 kΩ
4.5 V to 5.5 V	4.5 V to 5.5 V	V _{CCi}	≤ 2.5 ns	50 pF	2.2 kΩ

[1] V_{CCi} is the supply voltage associated with the input.

13 Application information

13.1 Applications

The NTSX2102 can be used in point-to-point applications to interface between devices or systems operating at different supply voltages. The device is targeted at I²C or 1-wire buses which use open-drain drivers.

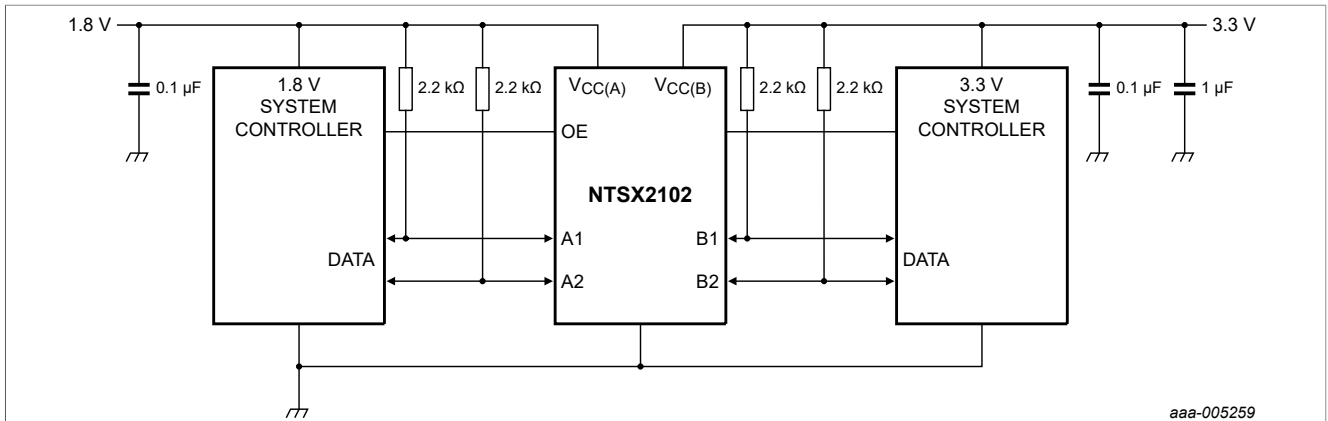


Figure 8. Typical voltage level-translation circuit

13.2 Architecture

The architecture of the NTSX2102 is shown in [Figure 9](#). The device does not require an extra input signal to control the direction of data flow from A to B or B to A. The NTSX2102 is a "switch" type voltage translator, it employs two key circuits to enable voltage translation:

1. Two pass-gate transistors (N-channel) that tie the ports together.
2. An output edge-rate accelerator that detects and accelerates rising and falling edges on the I/O pins (see [Figure 10](#)).

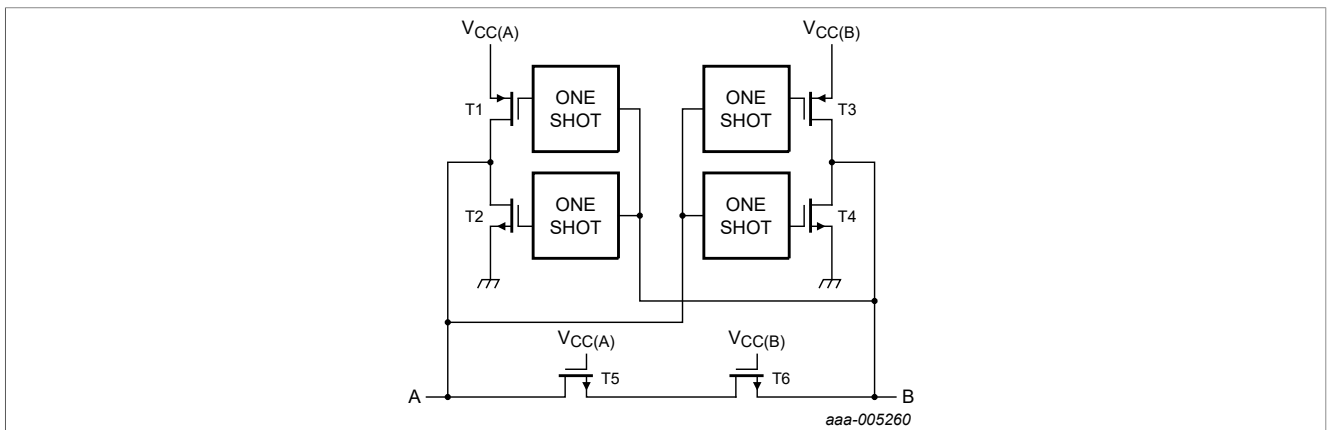


Figure 9. Architecture of NTSX2102 I/O cell (one channel)

During an input transition, a one-shot accelerates the output transition by switching on the PMOS transistors (T1, T3) for a LOW-to-HIGH transition. Alternatively, it switches on the NMOS transistors (T2, T4) for a HIGH-to-LOW transition. Once activated, the one-shot is de-activated after approximately 25 ns (see [Figure 11](#)). During the acceleration time, the driver output resistance is between approximately 10 Ω and 35 Ω. To avoid signal contention, the application must not exceed the maximum data rate or wait for the one-shot circuit to turn-off, before applying a signal in the opposite direction.

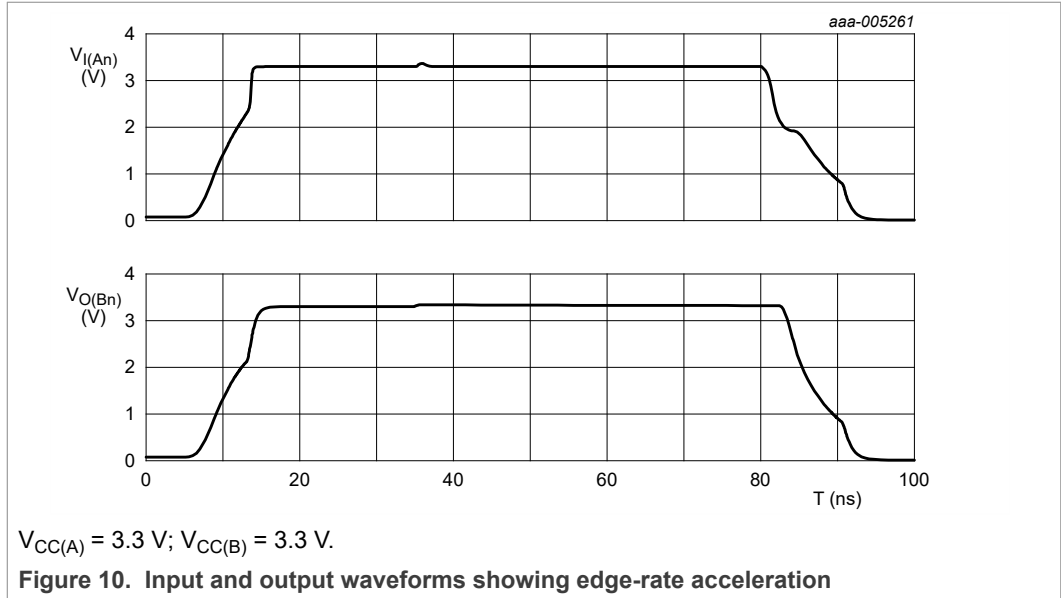


Figure 10. Input and output waveforms showing edge-rate acceleration

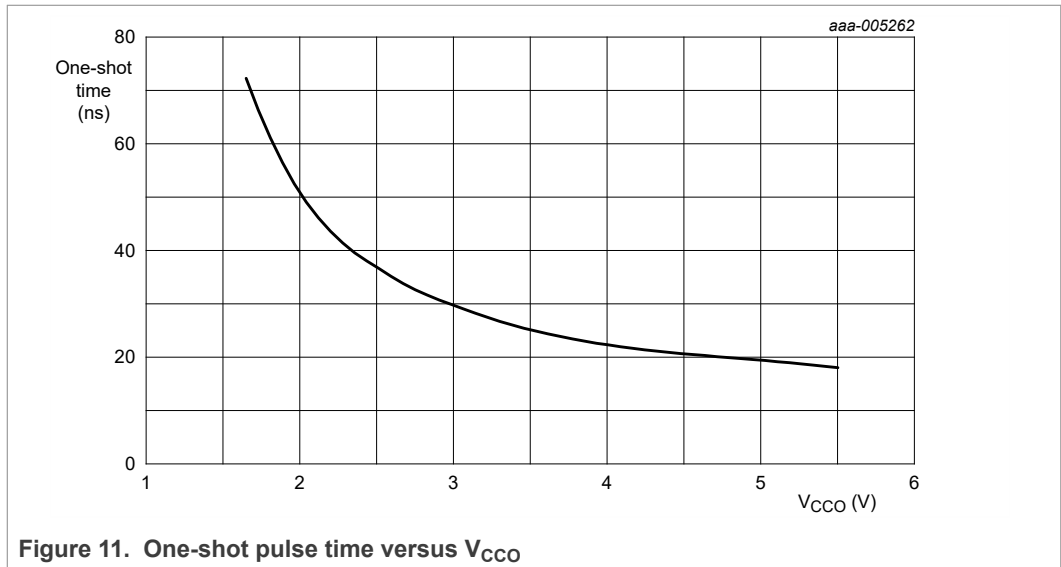


Figure 11. One-shot pulse time versus V_{CCO}

13.3 Input driver requirements

As the NTSX2102 is a switch type translator, properties of the input driver directly affect the output signal. The external open-drain driver applied to an I/O, determines the static current sinking capability of the system. The maximum data rate, output transition times (t_{THL} , t_{TLH}) and propagation delays (t_{PHL} , t_{PLH}) are dependent upon the output impedance and edge-rate of the external driver.

13.4 Output load considerations

The maximum lumped capacitive load that can be driven is dependent upon the one-shot pulse duration and has been tuned to 600 pF. In cases with higher capacitive loading, there is a risk that the output does not reach the positive rail within the one-shot pulse

duration. To avoid excessive capacitive loading and to ensure correct triggering of the one-shot, use short trace lengths and low capacitance connectors on NTSX2102 PCB layouts. The length of the PCB trace should be such that the round-trip delay of any reflection is within the one-shot pulse duration. Such a length ensures low impedance termination and avoids output signal oscillations and one-shot retriggering.

13.5 Output enable (OE)

An output enable input (OE) is used to disable the device. Setting OE = LOW causes all I/Os to assume the high-impedance OFF-state.

13.6 Power-up

When either of the supplies $V_{CC(n)}$ is at 0 V, outputs are in the high-impedance OFF-state. One of the advantages of NTSX translators is that either $V_{CC(A)}$ or $V_{CC(B)}$ may be powered up first. To reduce dissipation during power-up, ensure that output enable (OE) is defined. Connect it via a pulldown resistor to GND or, if the application allows, hardwired to $V_{CC(A)}$. If the OE pin is hardwired to $V_{CC(A)}$, either supply can be powered up or down first. If a pulldown is used, the following sequences are recommended.

For power-up:

1. Apply power to either supply pin
2. Apply power to other supply pin
3. Enable the device by driving OE HIGH

For power down:

1. Disable the device by driving OE LOW
2. Remove power from either supply pin
3. Remove power from other supply pin

13.7 Pull-up resistors on I/O lines

Each A port I/O requires a pull-up resistor to $V_{CC(A)}$, and each B port I/O requires a pull-up resistor to $V_{CC(B)}$. Choose the magnitude of the pull-up resistors to ensure that the output voltage levels meet the application requirement.

14 Package outline

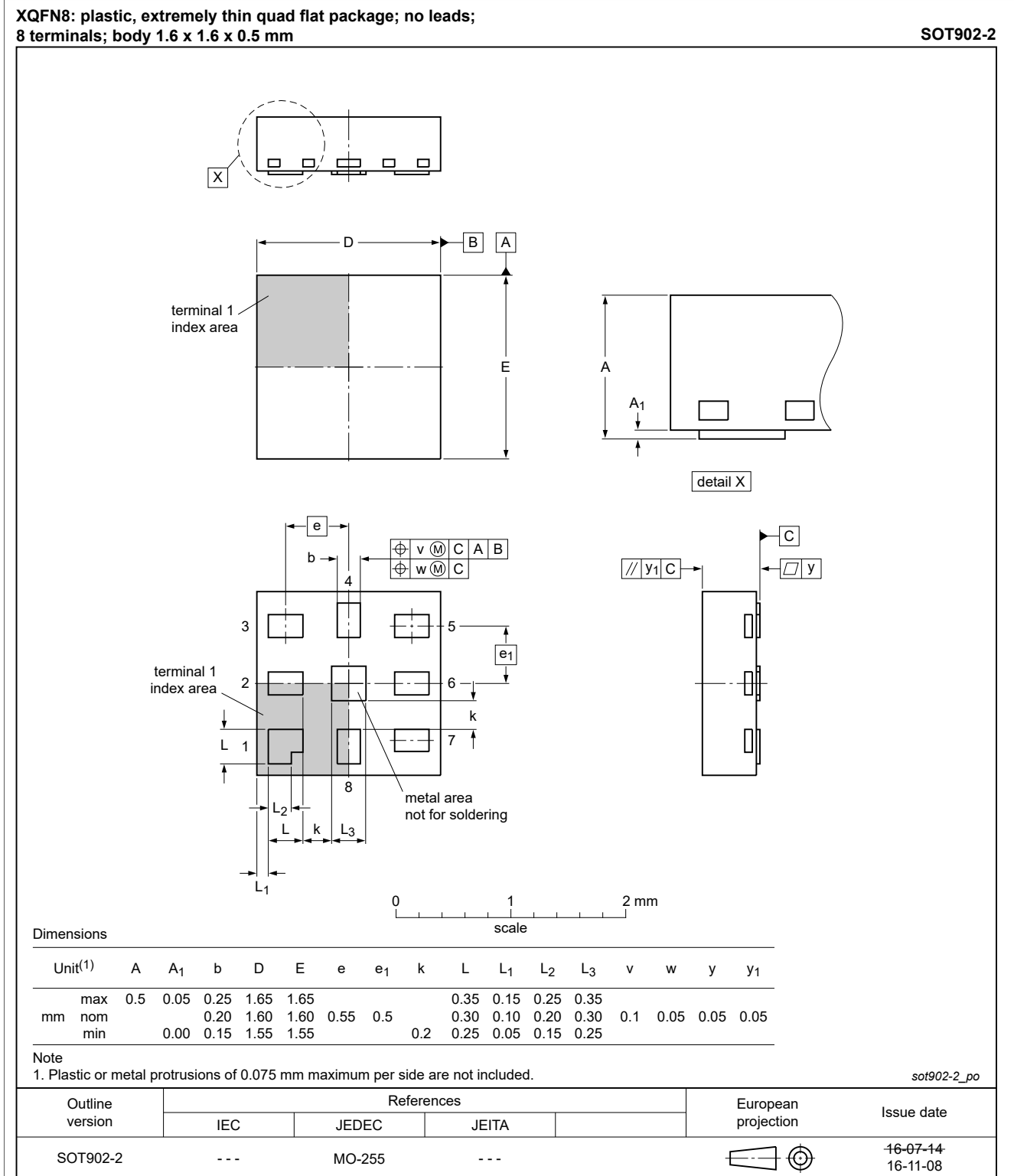


Figure 12. Package outline SOT902-2 (XQFN8)

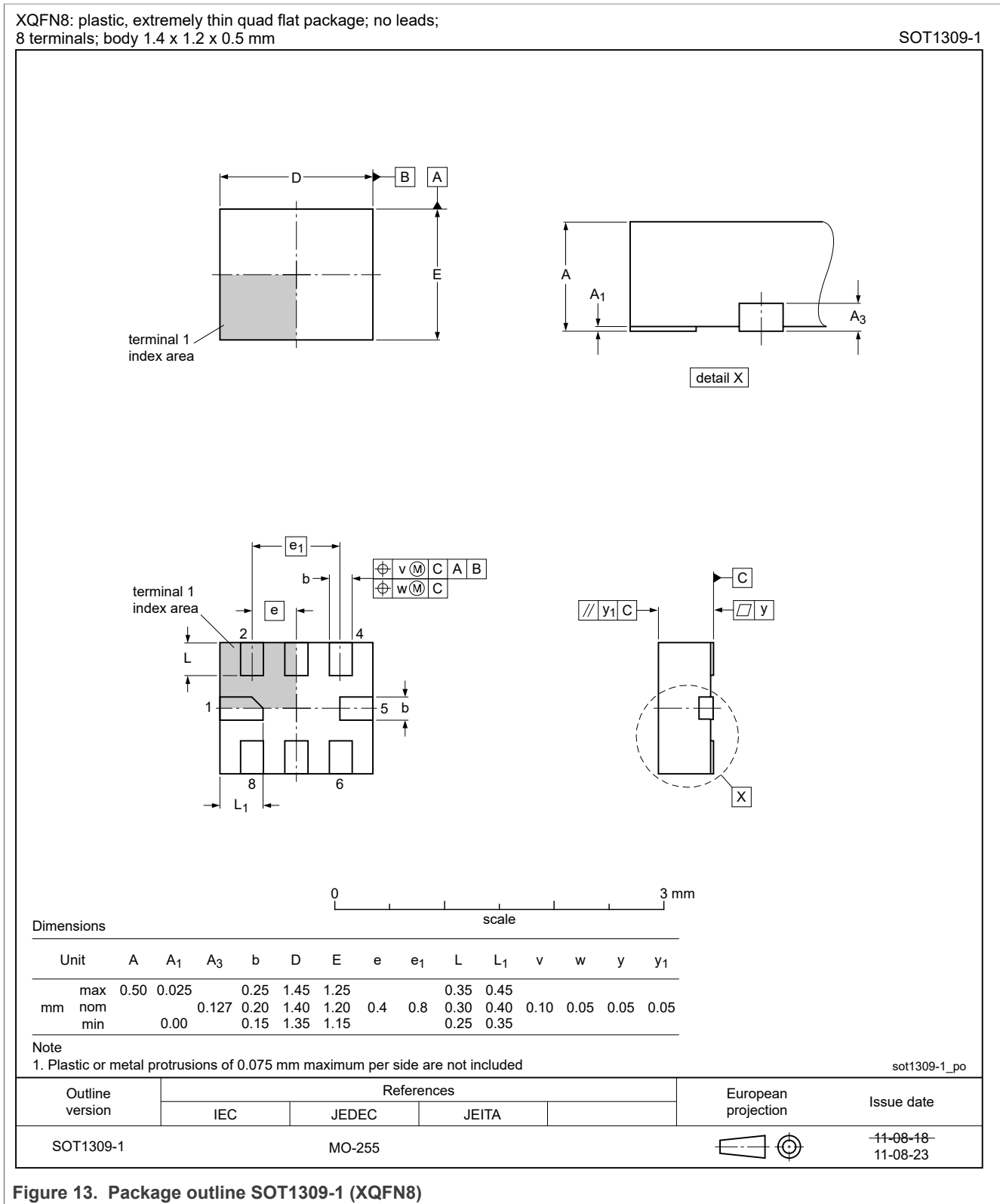


Figure 13. Package outline SOT1309-1 (XQFN8)

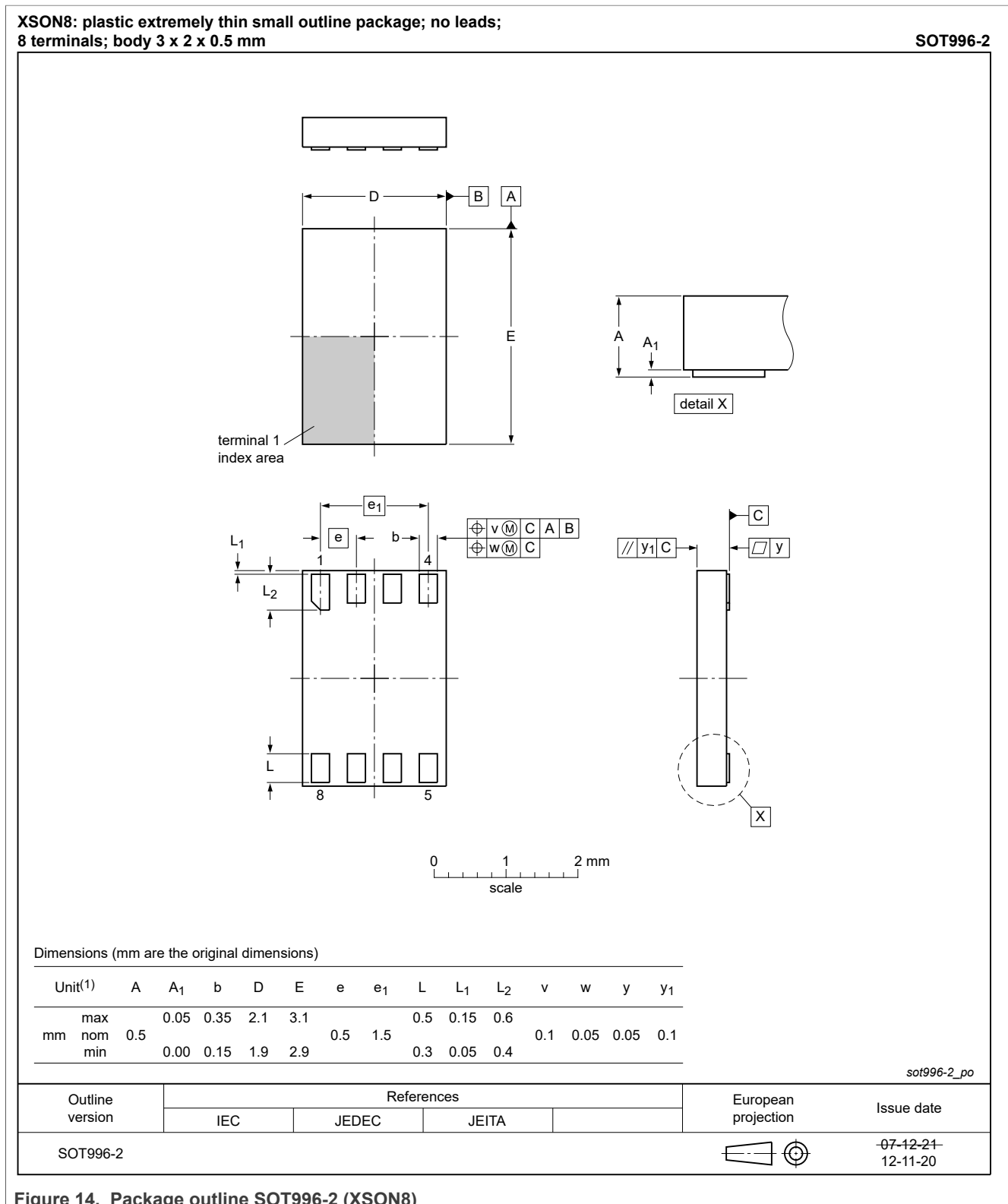


Figure 14. Package outline SOT996-2 (XSON8)

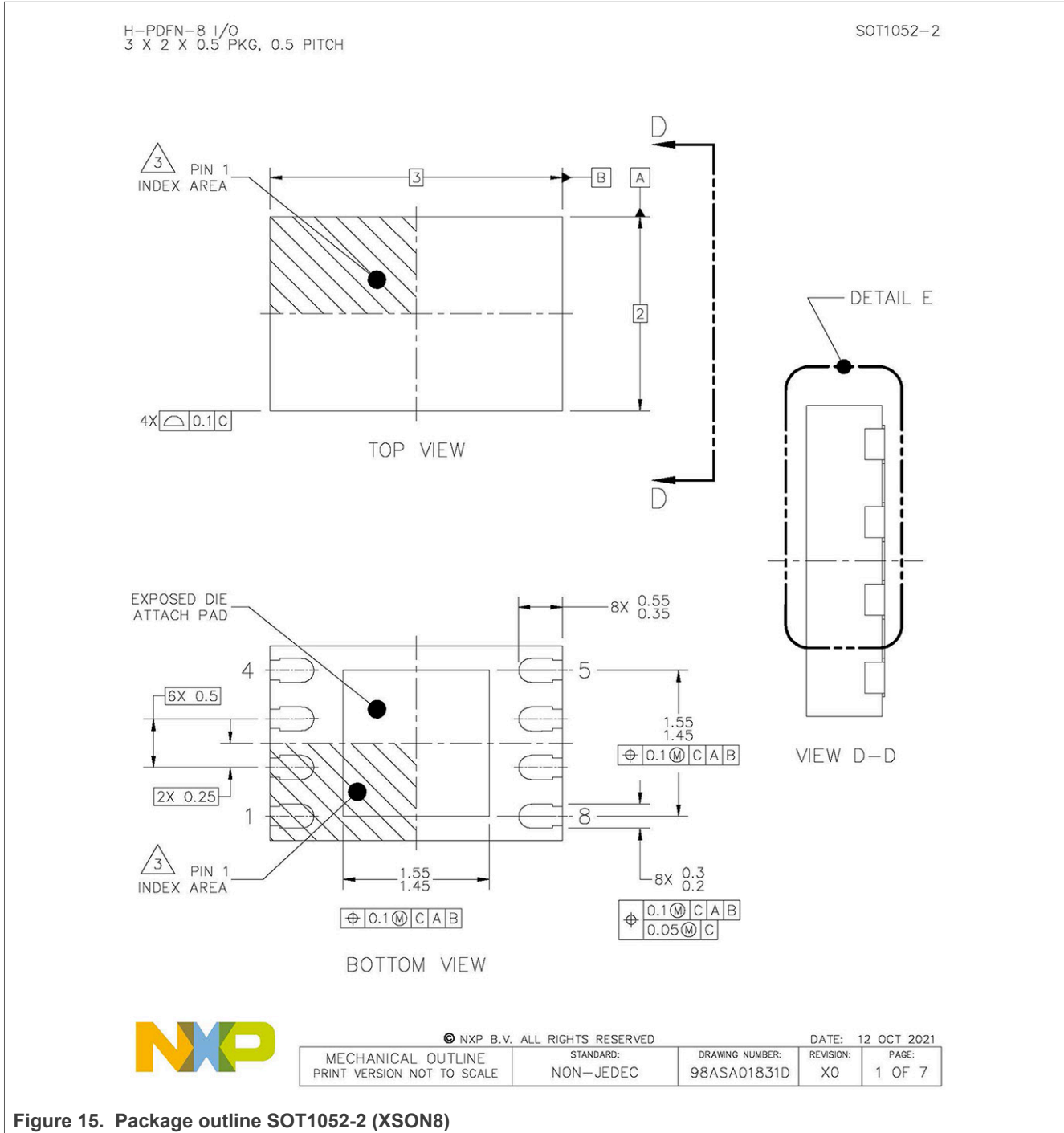


Figure 15. Package outline SOT1052-2 (XSON8)

15 Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
GPIO	General Purpose Input Output
HBM	Human Body Model
I ² C	Inter-Integrated Circuit
PCB	Printed-circuit board
PMOS	Positive Metal Oxide Semiconductor
SMBus	System Management Bus
UART	Universal Asynchronous Receiver Transmitter
UTLP	Ultra Thin Leadless Package

16 Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NTSX2102 v.2.1	20211112	Product data sheet	—	NTSX2102 v.2
Modifications:	<ul style="list-style-type: none"> • Section 4, Table 1, revised as follows: <ul style="list-style-type: none"> – Revised the ordering information table to conform to the standard NXP ordering information table, moving the temperature information to Section 4.1, Table 2. – Added footnote for discontinuation notice. – Inserted new column titled "Topside marking" and removed the first level section titled "Marking". – NTSX2102GM: removed part number from the table. – NTSX2102TL: added new part number to the table. • Section 4.1, added new section. • Section 6.1, Figure 4, removed pin configuration for SOT902-2 and added pin configuration for SOT1052-2. • Section 14, revised as follows: <ul style="list-style-type: none"> – Figure 12, Figure 13, Figure 14, updated the images in each figure. – Figure 15, added new package outline figure for SOT1052-2. 			
NTSX2102 v.2	20130211	Product data sheet	—	NTSX2102 v.1.1
NTSX2102 v.1.1	20121121	Product data sheet	—	NTSX2102 v.1
NTSX2102 v.1	20121119	Product data sheet	—	—

17 Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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